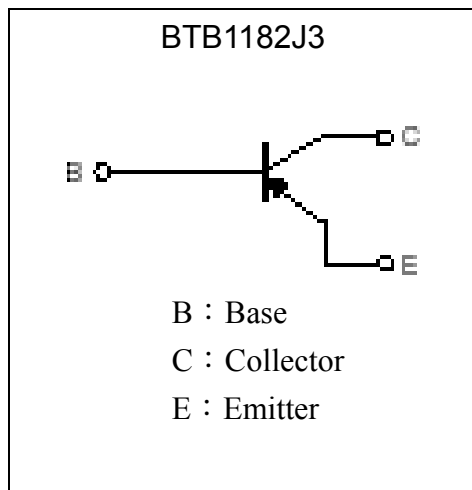
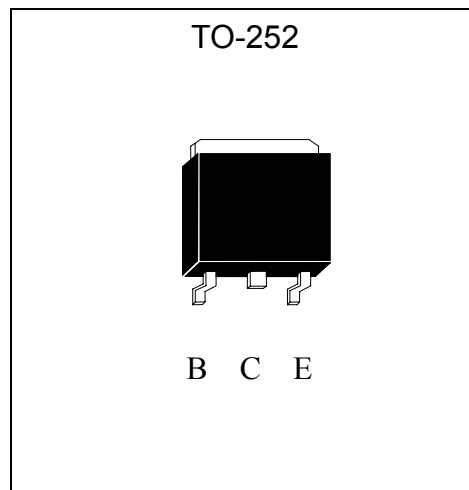


**Low Vcesat PNP Epitaxial Planar Transistor**

# BTB1182J3

**Features**

- Low  $V_{CE(sat)}$ ,  $V_{CE(sat)} = -0.7$  V (typical), at  $I_C / I_B = -2$  A /  $-0.5$  A
- Excellent current gain characteristics
- Complementary to BTB1758J3

**Symbol**

**Outline**

**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	$V_{CBO}$	-40	V
Collector-Emitter Voltage	$V_{CEO}$	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current (DC)	$I_C$	-2	A
Collector Current (Pulse)	$I_{CP}$	-5 (Note)	A
Power Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_d$	10	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

 Note : Single Pulse ,  $P_w = 10$ ms



**Characteristics (Ta=25°C)**

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV <sub>CBO</sub>	-40	-	-	V	I <sub>C</sub> =-50μA, I <sub>E</sub> =0
BV <sub>CEO</sub>	-30	-	-	V	I <sub>C</sub> =-1mA, I <sub>B</sub> =0
BV <sub>EBO</sub>	-5	-	-	V	I <sub>E</sub> =-50μA, I <sub>C</sub> =0
I <sub>CBO</sub>	-	-	-1	μA	V <sub>CB</sub> =-20V, I <sub>E</sub> =0
I <sub>EBO</sub>	-	-	-1	μA	V <sub>EB</sub> =-4V, I <sub>C</sub> =0
*V <sub>CE(sat)</sub>	-	-	-1	V	I <sub>C</sub> =-3A, I <sub>B</sub> =-0.1A
*h <sub>FE</sub>	82	-	560	-	V <sub>CE</sub> =-3V, I <sub>C</sub> =-0.5A
f <sub>T</sub>	-	100	-	MHz	V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.1A, f=100MHz
C <sub>ob</sub>	-	50	-	pF	V <sub>CB</sub> =-10V, f=1MHz

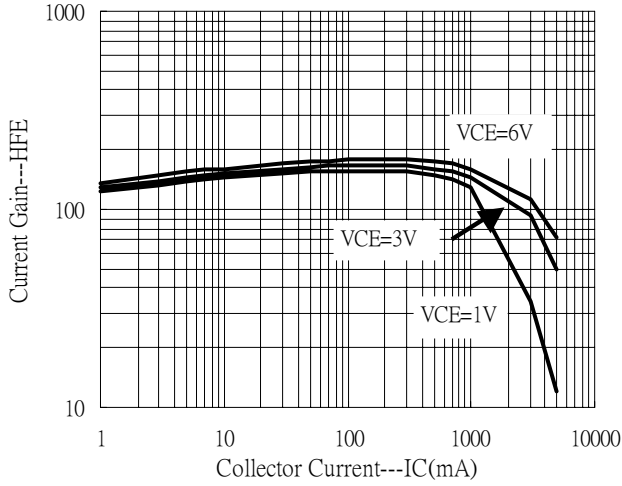
\*Pulse Test : Pulse Width ≤380us, Duty Cycle ≤2%

**Classification Of hFE**

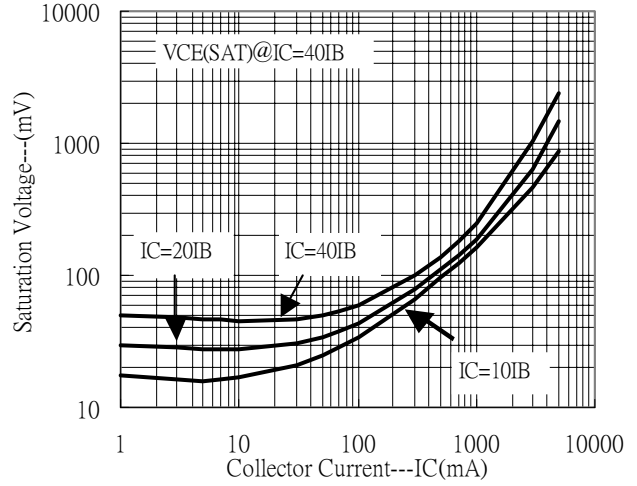
Rank	P	Q	R	S
Range	82~180	120~270	180~390	270~560

## Characteristic Curves

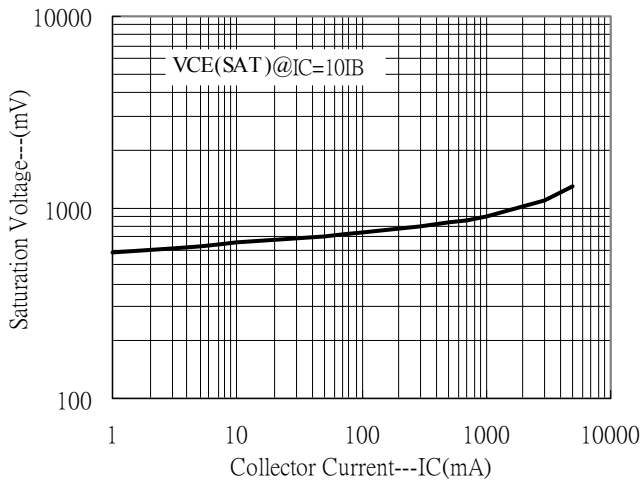
Current Gain vs Collector Current



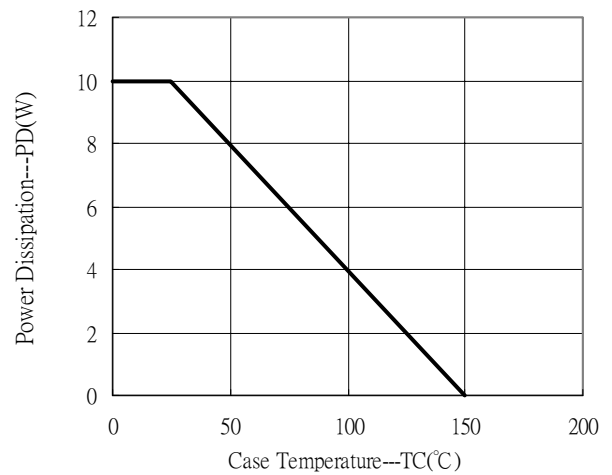
Saturation Voltage vs Collector Current



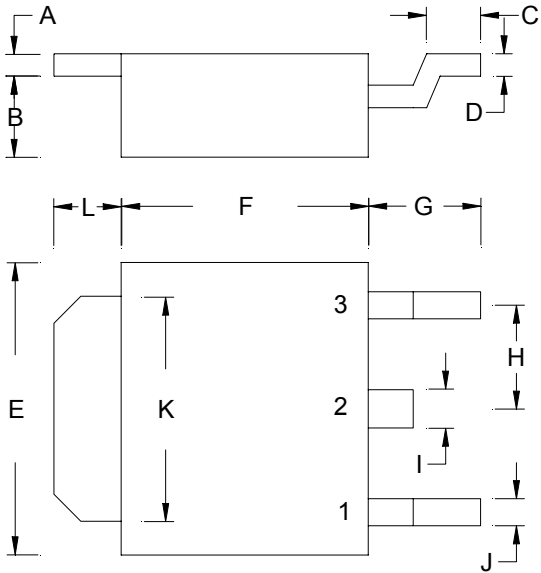
Saturation Voltage vs Collector Current



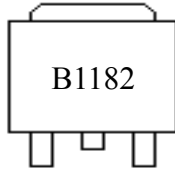
Power Derating Curve



**TO-252 Dimension**



Marking:



Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead TO-252 Plastic Surface Mount Package  
 CYStek Package Code: J3

\*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0177	0.0217	0.45	0.55	G	0.0866	0.1102	2.20	2.80
B	0.0650	0.0768	1.65	1.95	H	-	*0.0906	-	*2.30
C	0.0354	0.0591	0.90	1.50	I	-	0.0354	-	0.90
D	0.0177	0.0236	0.45	0.60	J	-	0.0315	-	0.80
E	0.2520	0.2677	6.40	6.80	K	0.2047	0.2165	5.20	5.50
F	0.2125	0.2283	5.40	5.80	L	0.0551	0.0630	1.40	1.60

- Notes: 1.Controlling dimension: millimeters.  
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.  
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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